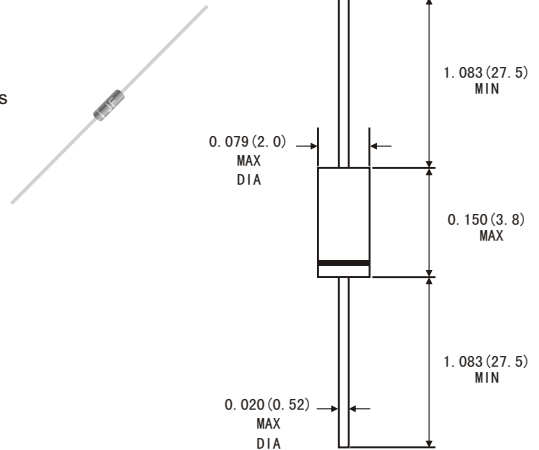


### FEATURES

- Metal-on-silicon junction
  - Low turn-on voltage
  - Ultrafast switching speed
  - Primarily intended for high level UHF mixers and ultrafast switching applications
- The diode is also available in the MiniMELF case with type designation LL19.
- High temperature soldering guaranteed: 260°C/10 seconds at terminals
  - Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC

### DO-35



Dimensions in inches and (millimeters)

### MECHANICAL DATA

- Case: DO-35 glass case
- Polarity: color band denotes cathode end
- Weight: Approx. 0.13 gram

### ABSOLUTE RATINGS(LIMITING VALUES)

	Symbols	Value	Units
Peak Reverse Voltage	$V_{RRM}$	10	V
Forward Continuous Current	$I_F$	30	mA
Surge non repetitive forward current $t_p \leq 1s$	$I_{FSM}$	60	mA
Junction and Storage temperature range	$T_{STG}$	-65 to +150	°C
	$T_J$	-65 to +150	°C
Maximum Lead Temperature for Soldering during 10s at 4mm from Case	$T_L$	230	°C

### ELECTRICAL CHARACTERISTICS

	Symbols	Min.	Typ.	Max.	Units
Reverse breakover voltage at $I_R=10\mu A$	$V_R$	10			V
					V
Leakage current at $V_R=5V$	$I_R$			100	nA
Forward voltage drop at $I_F=1mA$ Test pulse: $t_p \leq 300\mu s$ $\delta < 2\%$ $I_F=35mA$	$V_F$ $V_F$			0.40	V
				1.0	V
Junction Capacitance at $V_R=0V$ , $f=1GHz$	$C_J$			1.2	pF
Thermal resistance	$R_{\theta JA}$			400	K/W

# RATINGS AND CHARACTERISTICS CURVES BAT19

Figure 1. Forward current versus forward voltage at low level (typical values)

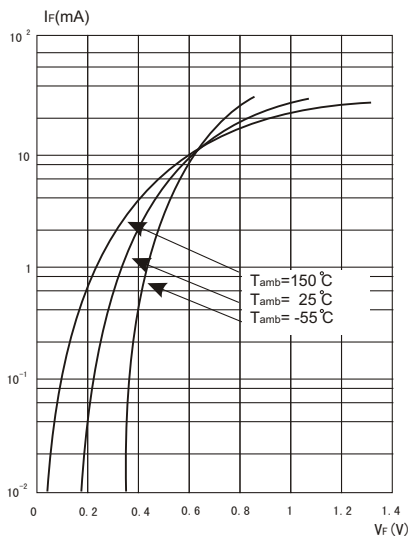


Figure 2. Capacitance C versus reverse applied voltage  $V_R$  (typical values)

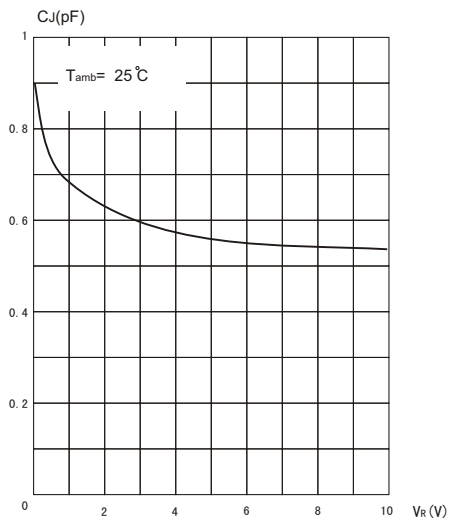


Figure 3. Reverse current versus ambient temperatures

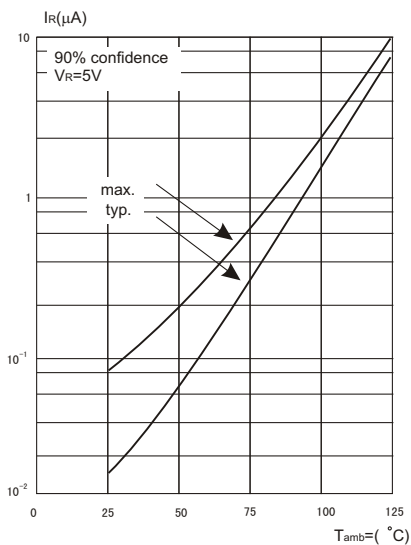


Figure 4. Reverse current versus continuous Reverse voltage (typical values)

